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# Information Disclosure Statement By Applicant

Substitute for form 1449/PTO

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Application Number: 10/760,090

Filing Date: 01/15/2004

First Named Inventor: King

Art Unit: 2815

Examiner Name: ~~N/A~~ WOJCIECHOWICZ

Attorney Docket Number: PROG2000-1C3

Examiner Initials	Patent Number	Publication Date	Inventor Name
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Examiner Name: ~~N.A. WATCHELOW~~ 1C7

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Examiner Name: ~~HA~~ *WATERHOUSE*

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